How2AppNote 010

eGaN® TECHNOLOGY

Achieving Best-in-class 48 V to 12 V, 60 A DC-DC Converter Performance with the EPC9130 Multiphase Buck



Motivation

Single-phase buck converter can work efficiently at output currents up to 25 A, but the power efficiency drops significantly at higher currents. A compact, cost effective, high-power and high-efficiency 48 V to 12 V buck converter, suitable for high-power computing and telecommunication applications, can be achieved by employing eGaN® FETs such as EPC2045 in a multiphase topology. The EPC9130 configured as a non-isolated, fully regulated five-phase synchronous buck converter yielded a power density of approximately 1000 W/in³ and a peak efficiency of 96.2%, and is capable of delivering up to 60 A (720 W) output.

EPC9130 five-phase 48 V to 12 V regulated intermediate bus converter

The EPC9130 development board is a 500 kHz switching frequency, 48 V nominal input voltage, 60 A maximum output current, 5-phase intermediate bus converter (IBC) with on-board microcontroller and gate drives, featuring the 100 V EPC2045 enhancement mode (eGaN[®]) field effect transistor (FET). The purpose of this development board is to provide a regulated 12 V power supply for high-power and high-performance applications showcasing the superior performance of the EPC2045 eGaN[®] FET. The block diagram is shown in figure 1.

The EPC9130 development board has five phases of two EPC2045 eGaN FETs in a half bridge configuration with a uPI Semiconductor UP1966A gate driver and supply and bypass capacitors. One single-phase power stage is shown in figure 2. The PWM signals to the gate drivers are fed by an on-board dsPIC33 microcontroller from Microchip[®]. The output voltage is regulated to 12 V. Basic voltage mode control of output is done with the microcontroller. Current sharing among the phases, under-voltage lockout as well as overcurrent, over-voltage, and over-temperature protection are available. To allow more flexible operation for this evaluation board, only current sharing and under-voltage lockout are implemented for this EPC9130 demo board.

EPC9130 experimental performance validation

The loss breakdown of the EPC9130 operating at 50 A output current is illustrated in figure 3 (left). The maximum FET temperature, as shown in figure 3 (right), is 86.1°C under 400 LFM airflow at 50 A. Figure 4 shows the efficiency curve against up to 60 A load when operating at 500 kHz, with a peak efficiency of 96.2% at 40 A load.



Figure 1: Block diagram of EPC9130 development board



Figure 2: Single-phase power stage

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25°C

eGaN[®] FET

EPC2045

Conclusions

Power Loss (W)

Switching

Inductor

Gate

Conduction

Migrating a high-power 48 V to 12 V intermediate bus converter design from Silicon MOSFETs to eGaN FETs offers reduction in both size and cost, while maintaining or exceeding efficiency targets. Table 1 sh the bill of materials that yields a cost per watt of less than \$0.04.

Suitable controllers for the EPC9130 include microcontrollers as the dsPIC33EP128GS704 from Microchip, which can generate complementary pairs of PWM signals.

The eGaN FET based 48 V to 12 V, 60 A load converter was demonstrated to yield a peak efficiency 96.2% with a power density of 1000 W/in with a cost below \$0.04 per watt. This same bill of materials can be used for output voltages as low as 5 V.



Body diode

Controller

Trace + Caps

Current sense

Max Temp. = 86.1°C 100°C

 $V_{IN} = 48 \text{ V}, V_{OUT} = 12 \text{ V}, I_{OUT} = 50 \text{ A}, f_{sw} = 500 \text{ kHz}$

Airflow





such sire	Inductor (3.3 μH)	5	IHLP5050EZER3R3M01
	Input Capacitors (1 µF 100 V)	20	C2012X7S2A105M125AB
	Output Capacitors (22 µF 25 V)	20	C2012X5R1E226M125AC
	Bulk Capacitors (180 μF 16 V)	3	16SVPF180M
	Gate Driver	5	uP1966A
	Controller	1	DSPIC33EP128GS704-E/ML
	Total		Less than \$0.04 per Watt
ated 1 ³ , all	Table 1: Bill of Materials for each phase of an eGaN FET based 48 V to 12 V five-phase		

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48 V - 12 V 60 A 5-phase Buck Converter

Component

eGaN® FET